# NXP BT169B SCR datasheet

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Planar passivated Silicon Controlled Rectifier with sensitive gate in a SOT54 (TO-92) plastic package. This SCR is designed to be interfaced directly to microcontrollers, logic ICs and other low power gate trigger circuits.

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#### 1. General description

Planar passivated Silicon Controlled Rectifier with sensitive gate in a SOT54 (TO-92) plastic package. This SCR is designed to be interfaced directly to microcontrollers, logic ICs and other low power gate trigger circuits.

#### 2. Features and benefits

- · Planar passivated for voltage ruggedness and reliability
- Sensitive gate
- Direct triggering from low power gate circuits and logic ICs

#### 3. Applications

- Ignition circuits
- Lighting ballasts
- Protection circuits
- Switched Mode Power Supplies

### 4. Quick reference data

Table 1. C	Quick reference data					
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
V <sub>DRM</sub>	repetitive peak off- state voltage		-	-	200	V
V <sub>RRM</sub>	repetitive peak reverse voltage		-	-	200	V
I <sub>TSM</sub>	non-repetitive peak on- state current	half sine wave; $T_{j(init)} = 25 \text{ °C};$ $t_p = 10 \text{ ms}; \text{ Fig. 4}; \text{ Fig. 5}$	-	-	8	A
I <sub>T(AV)</sub>	average on-state current	half sine wave; T <sub>lead</sub> ≤ 83 °C; <u>Fig. 1</u>	-	-	0.5	A
I <sub>T(RMS)</sub>	RMS on-state current	half sine wave; T <sub>lead</sub> ≤ 83 °C; <u>Fig. 2;</u> <u>Fig. 3</u>	-	-	0.8	A
Static chara	acteristics	· /				
I <sub>GT</sub>	gate trigger current	$V_D$ = 12 V; I <sub>T</sub> = 10 mA; T <sub>j</sub> = 25 °C; Fig. 7	-	50	200	μA





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## 5. Pinning information

Table 2.	Pinning	information				
Pin	Symbol	Description	Simplified outline	Graphic symbol		
1	А	anode		А <del>-Ң</del> К		
2	G	gate		G sym037		
3	К	cathode				
			TO-92 (SOT54)			

## 6. Ordering information

Table 3. Ordering information						
Type number	Package					
	Name	Description	Version			
BT169B	TO-92	plastic single-ended leaded (through hole) package; 3 leads	SOT54			

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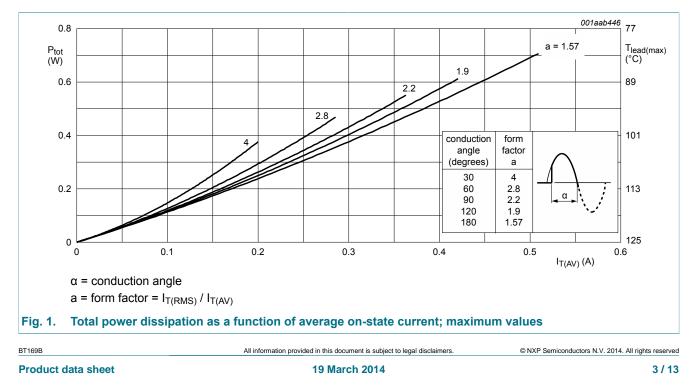
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## 7. Limiting values

#### Table 4.Limiting values

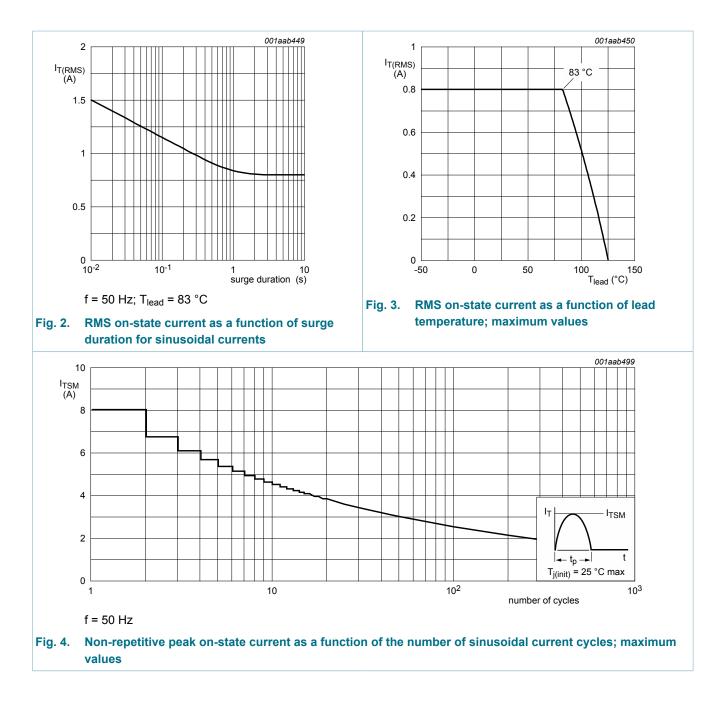
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Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>DRM</sub>	repetitive peak off-state voltage		-	200	V
V <sub>RRM</sub>	repetitive peak reverse voltage		-	200	V
I <sub>T(AV)</sub>	average on-state current	half sine wave; $T_{lead} \le 83 \text{ °C}$ ; Fig. 1	-	0.5	А
I <sub>T(RMS)</sub>	RMS on-state current	half sine wave; T <sub>lead</sub> ≤ 83 °C; <u>Fig. 2;</u> <u>Fig. 3</u>	-	0.8	A
I <sub>TSM</sub>	non-repetitive peak on-state current	half sine wave; $T_{j(init)} = 25 \text{ °C};$ $t_p = 10 \text{ ms}; \text{ Fig. 4}; \text{ Fig. 5}$	-	8	A
		half sine wave; $T_{j(init)}$ = 25 °C; $t_p$ = 8.3 ms	-	9	A
l <sup>2</sup> t	I <sup>2</sup> t for fusing	t <sub>p</sub> = 10 ms; SIN	-	0.32	A <sup>2</sup> s
dl <sub>T</sub> /dt	rate of rise of on-state current	$I_T$ = 2 A; $I_G$ = 10 mA; $dI_G/dt$ = 100 mA/ µs	-	50	A/µs
I <sub>GM</sub>	peak gate current		-	1	А
V <sub>RGM</sub>	peak reverse gate voltage		-	5	V
P <sub>GM</sub>	peak gate power		-	2	W
P <sub>G(AV)</sub>	average gate power	over any 20 ms period	-	0.1	W
T <sub>stg</sub>	storage temperature		-40	150	°C
Tj	junction temperature		-	125	°C



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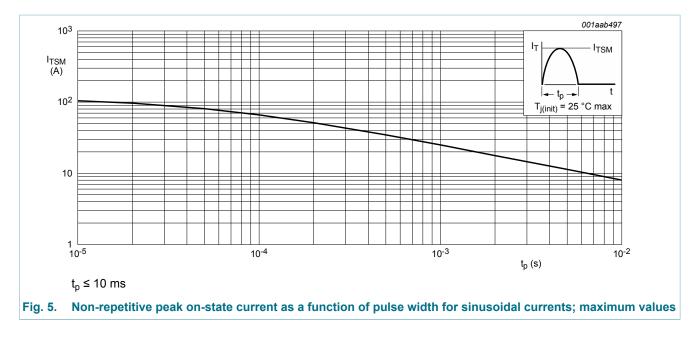
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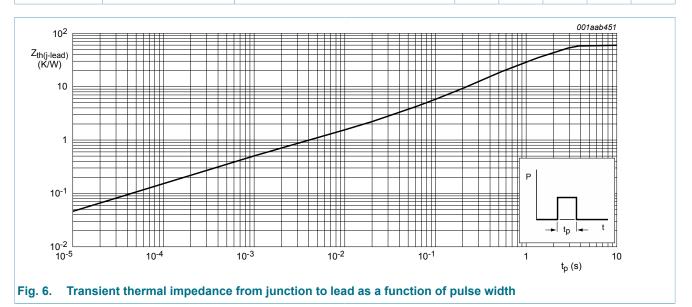
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#### 8. Thermal characteristics

Table 5. Th	ermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
$R_{th(j-lead)}$	thermal resistance from junction to lead	Fig. 6	-	-	60	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	printed circuit board mounted: lead length = 4 mm	-	150	-	K/W



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## 9. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics	· · · · · · · · · · · · · · · · · · ·	· · ·			
I <sub>GT</sub>	gate trigger current	$V_D$ = 12 V; I <sub>T</sub> = 10 mA; T <sub>j</sub> = 25 °C; Fig. 7	-	50	200	μA
IL	latching current	$V_D$ = 12 V; I <sub>G</sub> = 0.5 mA; R <sub>GK</sub> = 1 kΩ; T <sub>j</sub> = 25 °C; Fig. 8	-	2	6	mA
I <sub>H</sub>	holding current	$V_D$ = 12 V; R <sub>GK</sub> = 1 kΩ; T <sub>j</sub> = 25 °C; Fig. 9	-	2	5	mA
V <sub>T</sub>	on-state voltage	I <sub>T</sub> = 1.2 A; T <sub>j</sub> = 25 °C; <u>Fig. 10</u>	-	1.25	1.7	V
V <sub>GT</sub>	gate trigger voltage	V <sub>D</sub> = 12 V; I <sub>T</sub> = 10 mA; T <sub>j</sub> = 25 °C; Fig. 11	-	0.5	0.8	V
		$V_D$ = 200 V; I <sub>T</sub> = 10 mA; T <sub>j</sub> = 125 °C; Fig. 11	0.2	0.3	-	V
I <sub>D</sub>	off-state current	$V_D$ = 200 V; $T_j$ = 125 °C; $R_{GK}$ = 1 k $\Omega$	-	0.05	0.1	mA
I <sub>R</sub>	reverse current	$V_R$ = 200 V; $T_j$ = 125 °C; $R_{GK}$ = 1 k $\Omega$	-	0.05	0.1	mA
Dynamic cl	naracteristics	· /		1		
dV <sub>D</sub> /dt	rate of rise of off-state voltage	$V_{DM}$ = 134 V; T <sub>j</sub> = 125 °C; R <sub>GK</sub> = 1 kΩ; (V <sub>DM</sub> = 67% of V <sub>DRM</sub> ); exponential waveform; Fig. 12	500	) 800	-	V/µs
		$V_{DM}$ = 134 V; T <sub>j</sub> = 125 °C; (V <sub>DM</sub> = 67% of V <sub>DRM</sub> ); exponential waveform; gate open circuit; Fig. 12	-	25	-	V/µs
t <sub>gt</sub>	gate-controlled turn-on time	$I_{TM} = 2 \text{ A}; V_D = 200 \text{ V}; I_G = 10 \text{ mA}; dI_G / dt = 0.1 \text{ A} / \mu \text{s}; T_j = 25 \text{ °C}$	-	2	-	μs
tq	commutated turn-off time	$\begin{split} V_{DM} &= 134 \text{ V};  \text{T}_{\text{j}} = 125 ^{\circ}\text{C};  \text{I}_{\text{TM}} = 1.6  \text{A}; \\ V_{\text{R}} &= 35 \text{ V};  (\text{dI}_{\text{T}}/\text{dt})_{\text{M}} = 30  \text{A}/\text{\mu}\text{s};  \text{dV}_{\text{D}}/ \\ \text{dt} &= 2  \text{V}/\text{\mu}\text{s};  \text{R}_{\text{GK}} = 1  \text{k}\Omega;  (\text{V}_{\text{DM}} = 67\%  \text{of} \\ \text{V}_{\text{DRM}}) \end{split}$	-	100	-	μs

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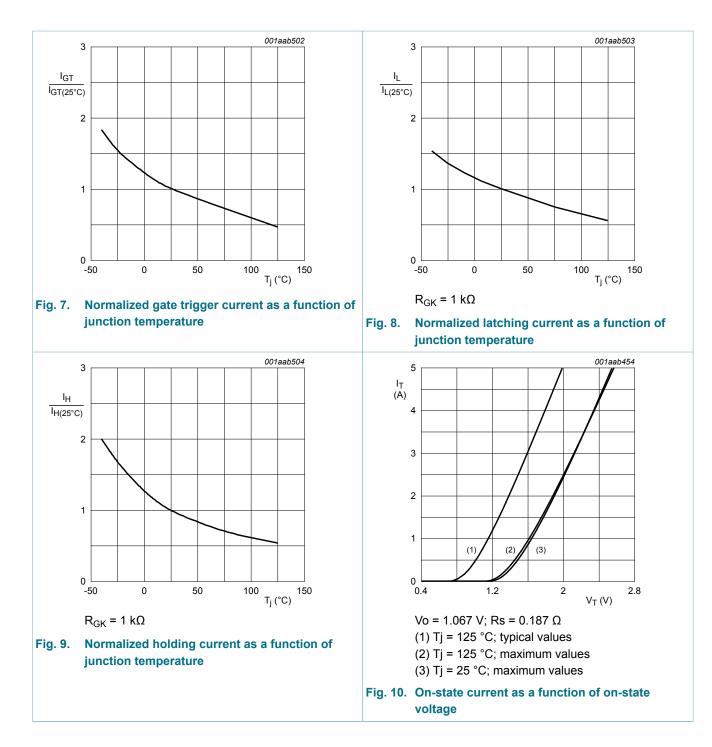
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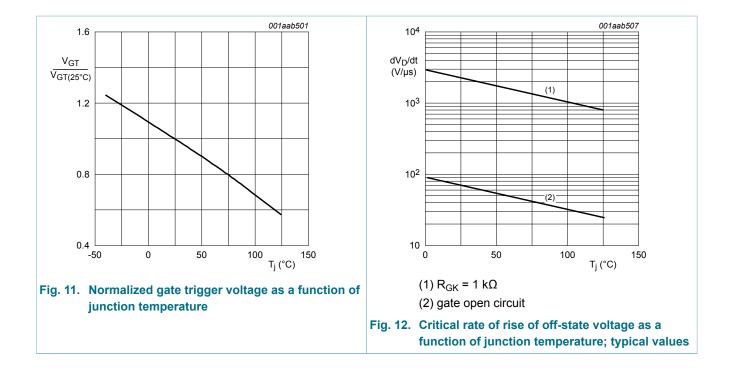
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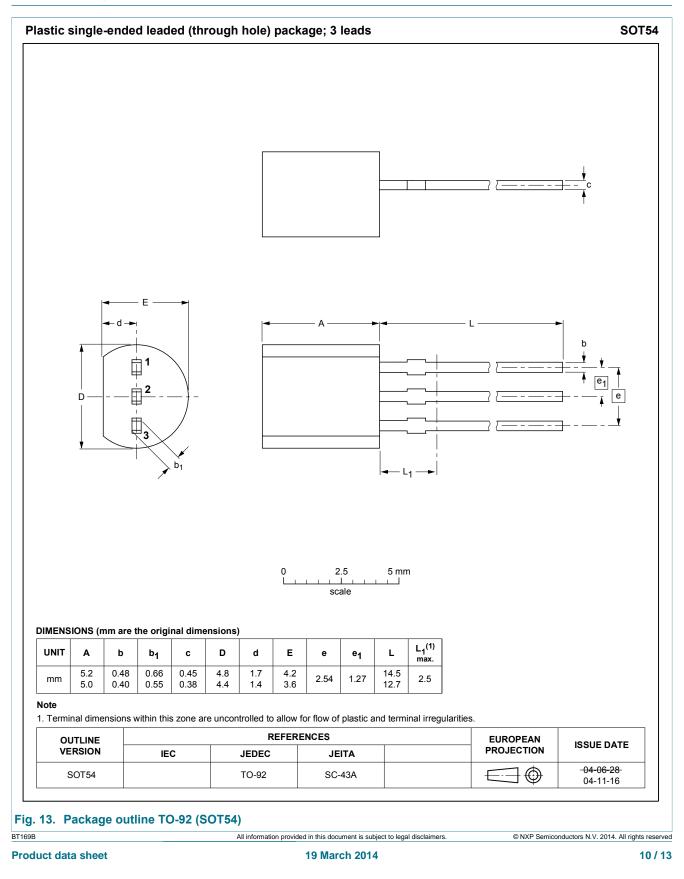
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## 10. Package outline



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